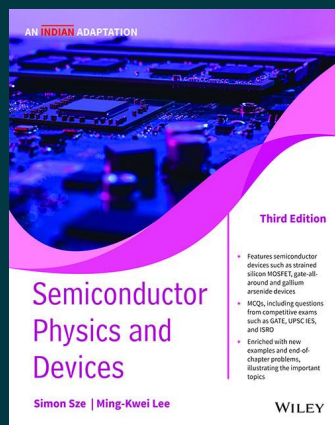




Semiconductor Physics And Devices, 3ed, An Indian Adaptation

By S. M. Sze, M. K. Lee

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Description

Semiconductor Physics and Devices is a comprehensive textbook written for the undergraduate students of electronics engineering, electrical engineering, applied science, and materials science. The book first provides a summary of the basic properties of semiconductor materials, covering energy band, carrier concentration, and transport properties, emphasizing silicon and gallium arsenide. It then examines p–n diodes, bipolar transistors, MOSFETs, and other field-effect transistors such as MESFETs, MODEFTs, negative-resistance and power devices, and photonic devices and sensors, including light-emitting diodes, photodetectors, and solar cells.

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